



Docket No. AM1562D1

#6/B
4/17/02
RW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

YIQIONG WANG

Serial No.: 09/882,141

Examiner: Umez-Eronini

Filed: June 15, 2001

Group Art Unit: 1765

For: METHOD OF ETCHING HIGH ASPECT
RATIO OPENINGS IN SILICON

AMENDMENT UNDER 37 CFR 1.115

To: Assistant Commissioner for Patents
Washington, DC 20231

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APR 16 2002
TC 1700

Sir:

This amendment is submitted in response to the office action mailed October 12, 2001. Please amend the above-identified application as follows.

IN THE CLAIMS

Claim 1 (Amended). An anisotropic etch mixture for a silicon substrate connected to a low power bias source consisting of one or more of a fluorine-containing gas selected from the group consisting of SF₆, Si₂F₆ and SiF₄ [together with], and HBr and oxygen.

Claim 4 (Amended). An etch mixture [according to claim 3 wherein the mixture additionally] for silicon consisting essentially of a